

N-Ch 150V Fast Switching MOSFETs
General Description

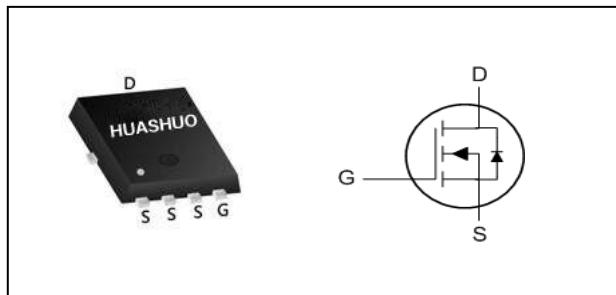
- 100% EAS Guaranteed
- Green Device Available
- Super Low RDS(ON)
- Advanced high cell density Trench technology

Product Summary

V _{DS}	150	V
R _{DS(ON),typ}	9.8	mΩ
I _D	75	A

Applications

- Load Switch
- LED Applications
- Networking Applications
- Quick Charger

PRPAK5*6 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	150	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _c =25°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	75	A
I _D @T _c =100°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	45	A
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	9.8	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ^{1,6}	7.8	A
I _{DM}	Pulsed Drain Current ²	180	A
EAS	Single Pulse Avalanche Energy ³	430	mJ
I _{AS}	Avalanche Current	41	A
P _D @T _c =25°C	Total Power Dissipation ⁴	125	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹	---	55	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	1	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	150	---	---	V
R _{DSS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =20A	---	9.8	13	mΩ
		V _{GS} =4.5V , I _D =20A	---	11	15	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.7	2.5	V
I _{bss}	Drain-Source Leakage Current	V _{DS} =120V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =120V , V _{GS} =0V , T _J =125°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	1.4	---	Ω
Q _g	Total Gate Charge	V _{DS} =75V , V _{GS} =4.5V , I _D =20A	---	39	---	nC
Q _{gs}	Gate-Source Charge		---	15	---	
Q _{gd}	Gate-Drain Charge		---	18	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =75V , V _{GS} =10V , R _G =6Ω, I _D =1A	---	12	---	ns
T _r	Rise Time		---	15	---	
T _{d(off)}	Turn-Off Delay Time		---	88	---	
T _f	Fall Time		---	149	---	
C _{iss}	Input Capacitance	V _{DS} =75V , V _{GS} =0V , f=1MHz	---	4180	---	pF
C _{oss}	Output Capacitance		---	291	---	
C _{rss}	Reverse Transfer Capacitance		---	25	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	71	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _s =1A , T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _f =20A, di/dt=100A/us,T _j =25°C	---	76	---	nS
Q _{rr}	Reverse Recovery Charge		---	250	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=50V,V_{GS}=10V,L=0.5mH,I_{AS}=41A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Package limitation current.



Typical Characteristics

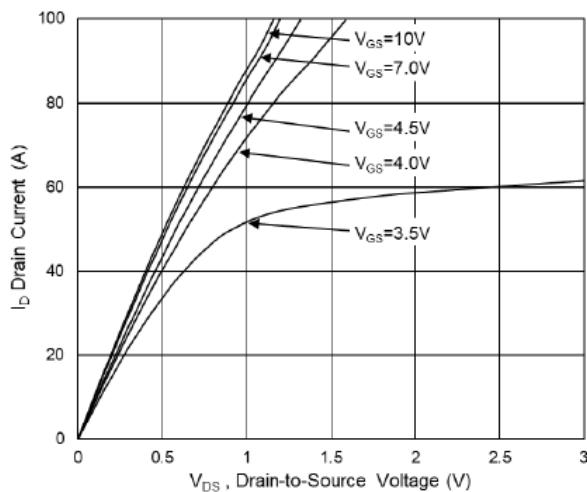


Fig.1 Typical Output Characteristics

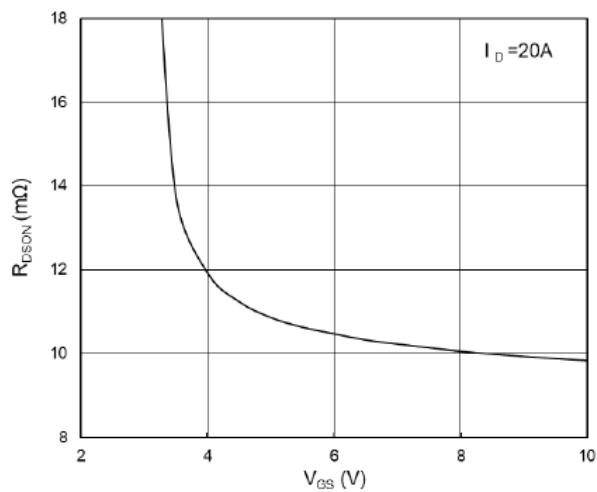


Fig.2 On-Resistance vs G-S Voltage

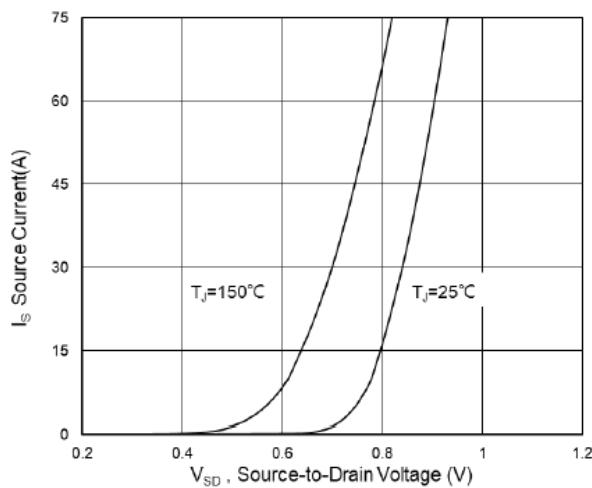


Fig.3 Source Drain Forward Characteristics

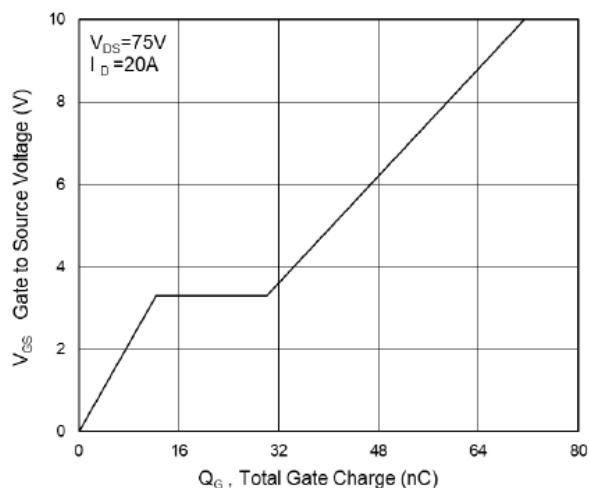


Fig.4 Gate-Charge Characteristics

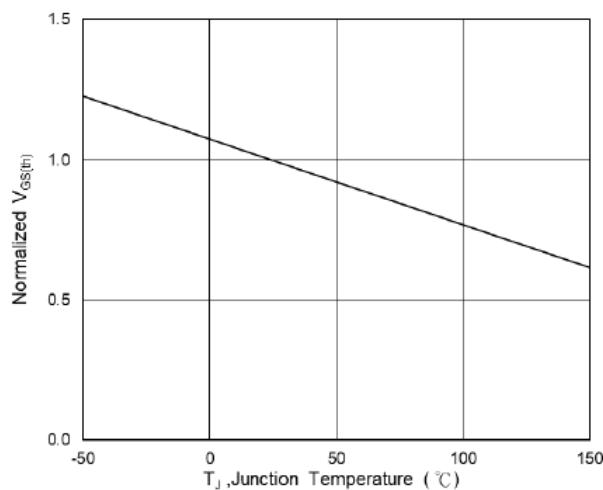


Fig.5 Normalized V_{TH} vs T_J

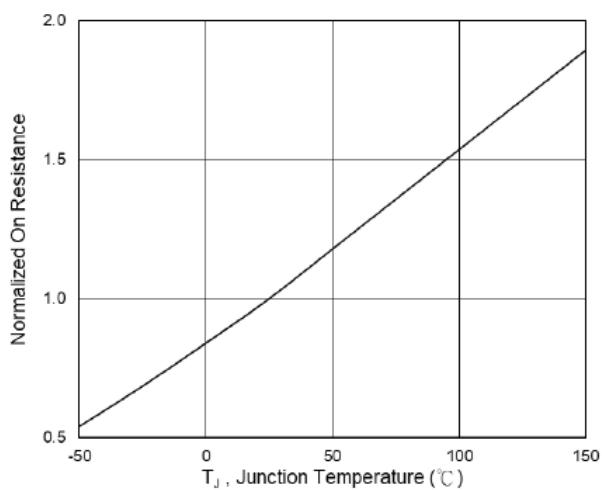


Fig.6 Normalized $R_{DS(on)}$ vs T_J



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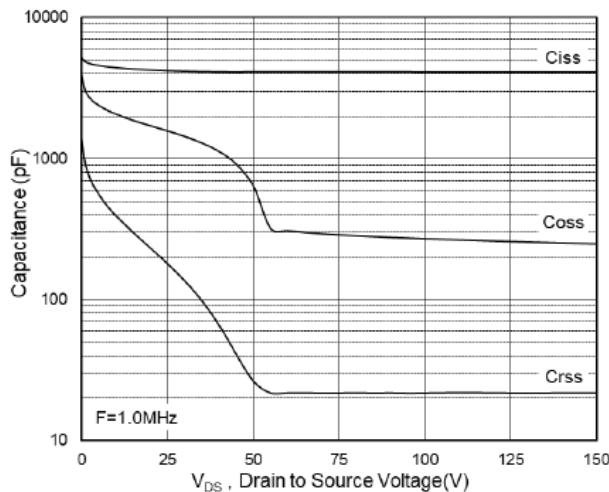


Fig.7 Capacitance

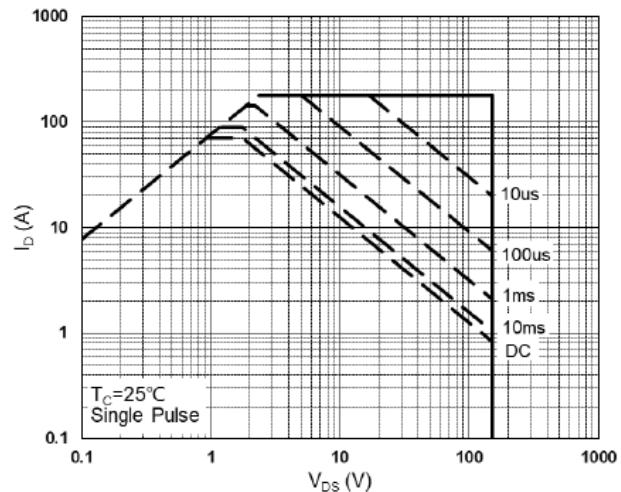


Fig.8 Safe Operating Area

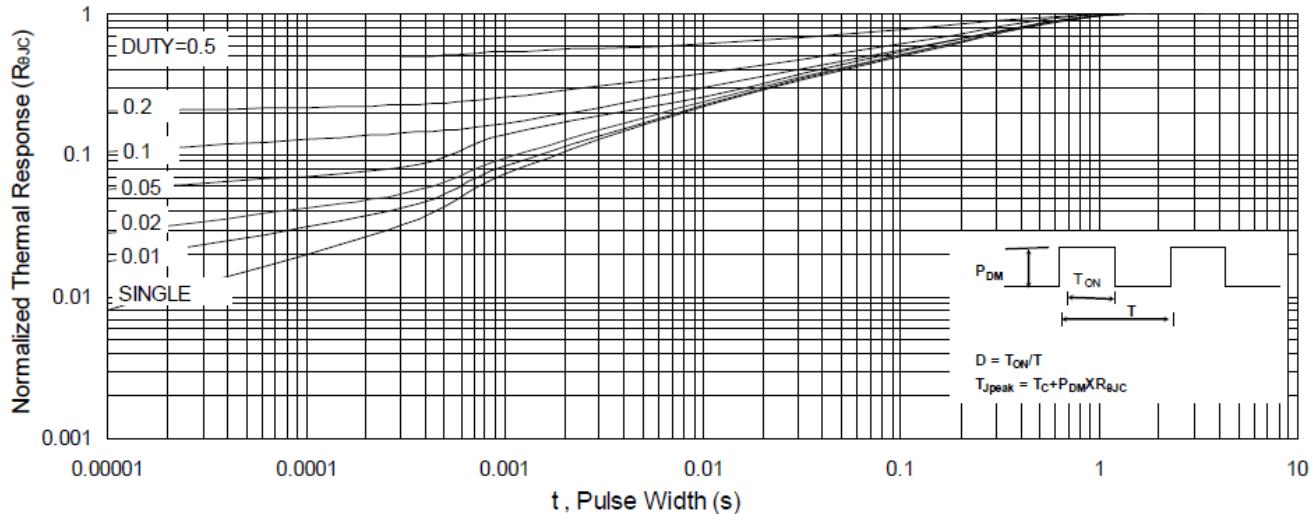


Fig.9 Normalized Maximum Transient Thermal Impedance

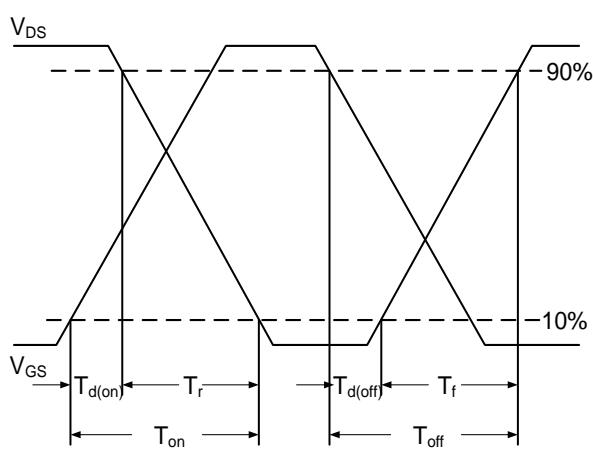


Fig.10 Switching Time Waveform

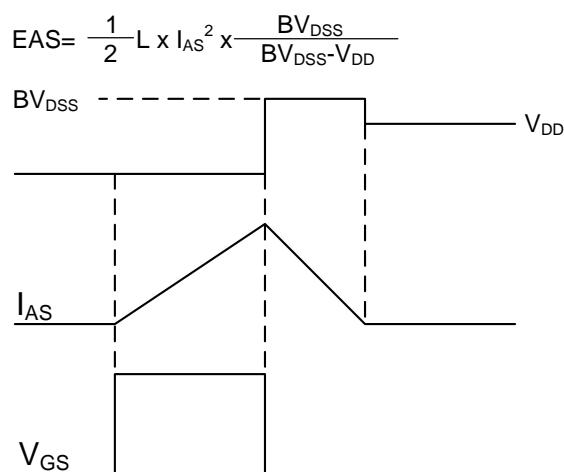
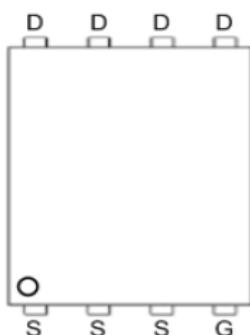
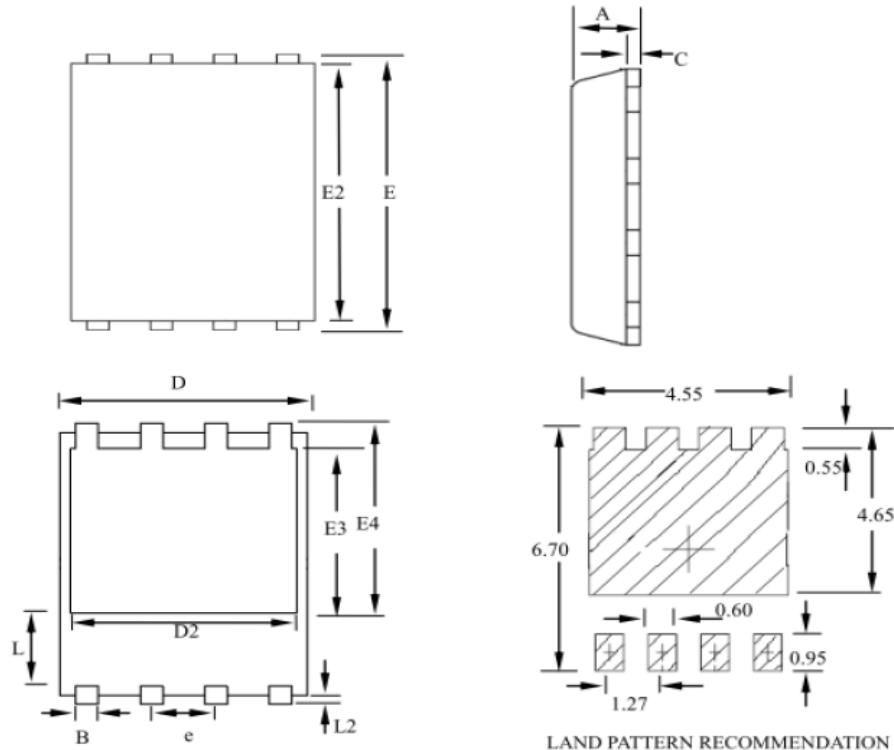


Fig.11 Unclamped Inductive Switching Waveform



Ordering Information

Part Number	Package code	Packaging
HSBA90N15	PRPAK5*6	3000/Tape&Reel



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	--	1.20	0.031	--	0.047
B	0.30	--	0.51	0.012	--	0.020
C	0.15	--	0.35	0.006	--	0.014
D	4.80	--	5.30	0.189	--	0.209
D2	3.61	--	4.35	0.142	--	0.171
E	5.90	--	6.35	0.232	--	0.250
E2	5.42	--	5.90	0.213	--	0.232
E3	3.23	--	3.90	0.127	--	0.154
E4	3.69	--	4.55	0.145	--	0.179
L	0.61	--	1.80	0.024	--	0.071
L2	0.05	--	0.36	0.002	--	0.014
e	--	1.27	--	--	0.050	--